

3DD69, 3DD71**NPN Silicon Low Frequency High Power Transistor****Features:**

1. Using triple-diffusion, low resistance liner process. Heavy out-put Current, small saturation voltage drop. Excellent out-put characteristic.
2. Implementation of standards: GJB33 A-97, QZJ840611A, QZJ840611
3. Use for Low-speed switch, power amplify, power adjustment, DC conversion.
4. Quality Class: JP, JT, JCT, GS, G, G+

TECHNICAL DATA:**(Ta = 25°C)**

Parameter name	Symbols	Unit	Specifications				
			3DD69			3DD71	
			A	B	C	D	E
Collector-Emitter Voltage	V_{CEO}	V	30	50	80	110	150
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	V	30	50	80	110	150
Emitter-Base Voltage	V_{EBO}	V	3			3	
Max. Collector Current	I_{CM}	A	10			15	
Max. Collector Dissipation	P_{CM}	W	100 ($T_c \leq 75^\circ\text{C}$)			150 ($T_c \leq 75^\circ\text{C}$)	
Junction Temperature	T_{jm}	$^\circ\text{C}$	175				
Storage Temperature	T_{stg}	$^\circ\text{C}$	-55~+175				
Collector-Emitter Leakage Current	I_{CEO}	mA	Max.:3.0 ($V_{CE}=20\text{V}$)				
Collector- Emitter Saturation Voltage Drop	$V_{CE(sat)}$	V	Max.:2.0 ($I_c=5\text{A}, I_B=1\text{A}$)			Max.:2.0 ($I_c=7.5\text{A}, I_B=1.5\text{A}$)	
DC Current Gain	h_{FE}		Min.:10 ($V_{CE}=10\text{V}, I_c=5\text{A}$)			Min.:10 ($V_{CE}=10\text{V}, I_c=7.5\text{A}$)	
E-Base Breakdown Voltage	$V_{(BR)EBO}$	V	≥ 3 ($I_E=20\text{mA}$)			≥ 3 ($I_E=20\text{mA}$)	

h_{FE} Colored:

Color	Brown	Red	Orange
h_{FE}	10~20	20~30	≥ 30

Outline and Dimensions: